



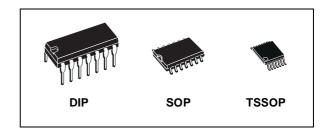
QUAD 2-INPUT AND GATE

- HIGH SPEED: t_{PD} = 13ns (TYP.) at V_{CC}=4.5V
- LOW POWER DISSIPATION: $I_{CC} = 1\mu A(MAX.)$ at $T_A=25^{\circ}C$
- COMPATIBLE WITH TTL OUTPUTS : $V_{IH} = 2V \text{ (MIN.) } V_{IL} = 0.8V \text{ (MAX)}$
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 4mA (MIN)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 08

DESCRIPTION

The M74HCT08 is an high speed CMOS QUAD 2-INPUT AND GATE fabricated with silicon gate $\mbox{C}^2\mbox{MOS}$ technology.

The internal circuit is composed of 2 stages including buffer output, which enables high noise immunity and stable output.



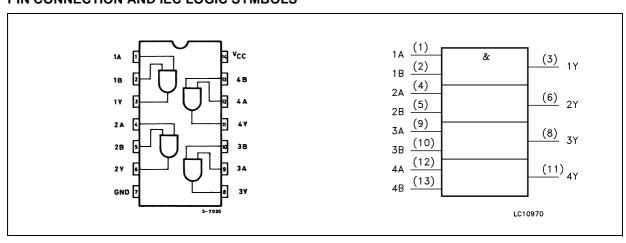
ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HCT08B1R	
SOP	M74HCT08M1R	M74HCT08RM13TR
TSSOP		M74HCT08TTR

The M74HCT08 is designed to directly interface HSC²MOS systems with TTL and NMOS components.

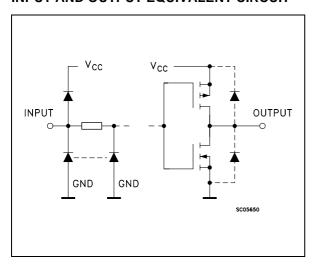
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



July 2001 1/8

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION				
1, 4, 9, 12	1A to 4A	Data Inputs				
2, 5, 10, 13	1B to 4B	Data Inputs				
3, 6, 8, 11	1Y to 4Y	Data Outputs				
7	GND	Ground (0V)				
14	V _{CC}	Positive Supply Voltage				

TRUTH TABLE

Α	В	Y
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied (*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	4.5 to 5.5	V
VI	Input Voltage	0 to V _{CC}	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
t _r , t _f	Input Rise and Fall Time (V _{CC} = 4.5 to 5.5V)	0 to 500	ns

DC SPECIFICATIONS

		1	Test Condition	Value							
Symbol	Symbol Parameter	v _{cc}		T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	4.5 to 5.5		2.0			2.0		2.0		V
V _{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	٧
V _{OH}	High Level Output	4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		V
	Voltage	4.5	I _O =-4.0 mA	4.18	4.31		4.13		4.10		V
V _{OL}	Low Level Output	4.5	I _O =20 μA		0.0	0.1		0.1		0.1	V
	Voltage	4.5	I _O =4.0 mA		0.17	0.26		0.33		0.40	V
II	Input Leakage Current	5.5	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μΑ
ΔI _{CC}	Additional Worst Case Supply Current	5.5	Per Input pin $V_I = 0.5V$ or $V_I = 2.4V$ Other Inputs at V_{CC} or GND $I_O = 0$			2.0		2.9		3.0	mA

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ns}$)

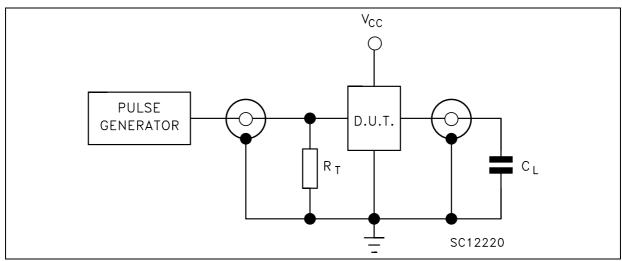
			est Condition	Value									
Symbol	Parameter	V _{CC} (V)	Vcc	Vcc		Т	_A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.			
t _{TLH} t _{THL}	Output Transition Time	4.5			8	15		19		22	ns		
t _{PLH} t _{PHL}	Propagation Delay Time	4.5			13	21		26		32	ns		

CAPACITIVE CHARACTERISTICS

		Test Condition		Value								
Symbol	Parameter	v _{cc}	Vcc	V _{CC}	T,	_A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
	(1)	(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
C _{IN}	Input Capacitance				5	10		10		10	pF	
C _{PD}	Power Dissipation Capacitance (note 1)				38						pF	

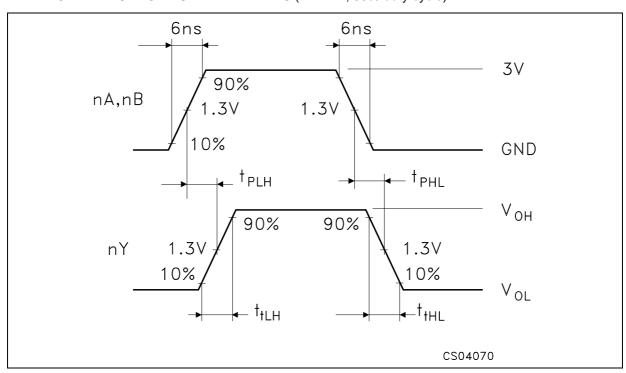
¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$ (per gate)

TEST CIRCUIT



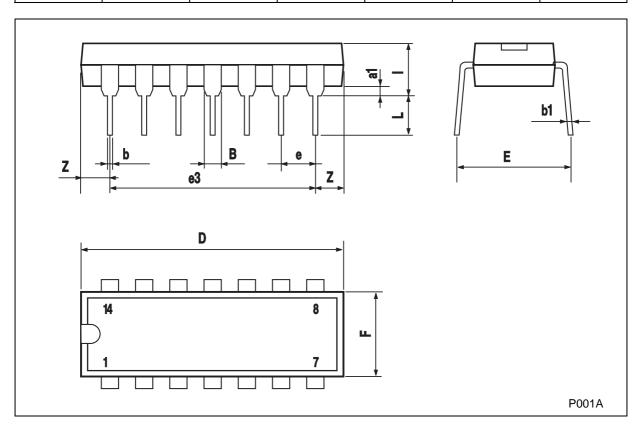
 C_L = 50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically 50 Ω)

WAVEFORM: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



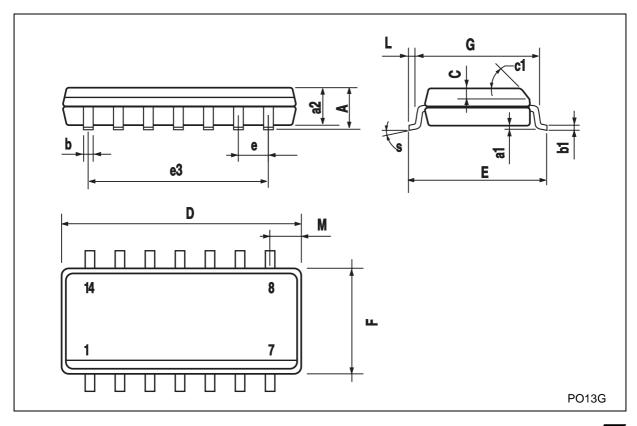
Plastic DIP-14 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



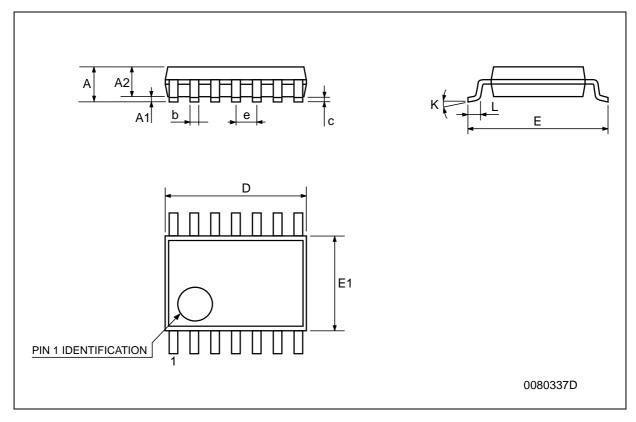
SO-14 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)	•	
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
еЗ		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.68			0.026
S			8° (ı	max.)		



TSSOP14 MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.2			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.8	1	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004		0.0089		
D	4.9	5	5.1	0.193	0.197	0.201		
E	6.2	6.4	6.6	0.244	0.252	0.260		
E1	4.3	4.4	4.48	0.169	0.173	0.176		
е		0.65 BSC			0.0256 BSC			
К	0°		8°	0°		8°		
L	0.45	0.60	0.75	0.018	0.024	0.030		



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